

## In the Claims

Claims 1-38 (Canceled).

39. (Currently Amended): Integrated circuitry comprising:

~~a substrate having a mean global outer surface extending along a plane;~~

~~the a~~ a substrate comprising a first conductive device component of a first type and being elongated in a first direction ~~generally parallel with the plane;~~

a second conductive device component of the first type and being elongated in a second direction ~~generally parallel with the plane~~, the first and second conductive device components at least predominately comprising common conductive material and being present as part of a finished construction of the integrated circuitry; and

the first and second conductive device components having different base widths in the finished circuitry construction, at least one of the first and second conductive device components ~~having a mean elevational axis which is angled~~ being beveled from perpendicular to the ~~plane~~ substrate along at least a majority of its elongated length in its respective first or second direction in the finished circuitry construction.

40. (Original): The integrated circuitry of claim 39 wherein the first and second directions are parallel with one another.

41. (Original): The integrated circuitry of claim 39 wherein the first and second directions are not parallel with one another.

42. (Original): The integrated circuitry of claim 39 wherein the first and second conductive device components entirely comprise common conductive material in at least one cross section.

43. (Currently Amended): The integrated circuitry of claim 39 wherein both the first and the second conductive device components are beveled ~~have a respective mean elevational axis which is elevationally angled~~ from perpendicular to the ~~plane~~ substrate along at least a majority of its elongated length in its respective first or second direction in the finished circuitry construction.

Claim 44 (Canceled).

45. (Currently Amended): The integrated circuitry of claim 39 wherein only one of the first and the second conductive device components is beveled ~~has a mean elevational axis which is angled~~ from perpendicular to the substrate along at least a majority of its elongated length in its respective first or second direction in the finished circuitry construction plane.

46. (New): Integrated circuitry comprising:  
a substrate comprising a first field effect transistor gate and being elongated in a first direction;  
a second field effect transistor gate and being elongated in a second direction, the first and second field effect transistor gates at least predominately comprising common conductive material and being present as part of a finished construction of the integrated circuitry; and  
the first and second field effect transistor gates having different base widths in the finished circuitry construction, at least one of the first and second field effect transistor gates being beveled from perpendicular to the substrate along at least a majority of its elongated length in its respective first or second direction in the finished circuitry construction.

47. (New): The integrated circuitry of claim 46 wherein the first and second directions are parallel with one another.

48. (New): The integrated circuitry of claim 46 wherein the first and second directions are not parallel with one another.

49. (New): The integrated circuitry of claim 46 wherein the first and second field effect transistor gates entirely comprise common conductive material in at least one cross section.

50. (New): The integrated circuitry of claim 46 wherein both the first and the second field effect transistor gates are beveled from perpendicular to the substrate along at least a majority of its elongated length in its respective first or second direction in the finished circuitry construction.

51. (New): The integrated circuitry of claim 46 wherein only one of the first and the second field effect transistor gates is beveled from perpendicular to the substrate along at least a majority of its elongated length in its respective first or second direction in the finished circuitry construction.

52. (New): Integrated circuitry comprising:

a substrate comprising a first conductive device component of a first type having a base and a top of first equal widths, and being elongated in a first direction;

a second conductive device component of the first type having a base and a top of second equal widths, and being elongated in a second direction, the first and second conductive device components at least predominately comprising common conductive material and being present as part of a finished construction of the integrated circuitry; and

the first and second widths being different in the finished circuitry construction, at least one of the first and second conductive device components being beveled from perpendicular to the substrate along at least a majority of its elongated length in its respective first or second direction in the finished circuitry construction.

53. (New): The integrated circuitry of claim 52 wherein the first and second directions are parallel with one another.

54. (New): The integrated circuitry of claim 52 wherein the first and second directions are not parallel with one another.

55. (New): The integrated circuitry of claim 52 wherein the first and second conductive device components entirely comprise common conductive material in at least one cross section.

56. (New): The integrated circuitry of claim 52 wherein both the first and the second conductive device components are beveled from perpendicular to the substrate along at least a majority of its elongated length in its respective first or second direction in the finished circuitry construction.

57. (New): The integrated circuitry of claim 52 wherein only one of the first and the second conductive device components is beveled from perpendicular to the substrate along at least a majority of its elongated length in its respective first or second direction in the finished circuitry construction.

58. (New): The integrated circuitry of claim 39 wherein the at least one conductive device component has opposing conductive sidewalls comprising respective substantially straight linear segments which are parallel with one another.

59. (New): The integrated circuitry of claim 46 wherein the at least one field effect transistor gate has opposing conductive sidewalls comprising respective substantially straight linear segments which are parallel with one another.

60. (New): The integrated circuitry of claim 52 wherein the at least one conductive device component has opposing conductive sidewalls comprising respective substantially straight linear segments which are parallel with one another.